ABSTRACT

To prevent an n-channel thin-film transistor from being deteriorated by hot holes generated in a gate-negative pulse mode. A thin polysilicon film 10 is provided with a p-type semiconductor region 13 in contact with a channel region 14. The p-type semiconductor region 13 is electrically connected to nowhere except the channel region 14. Holes induced on the surface due to a gate-negative pulse are further supplied from the p-type semiconductor region 13. An electric field established by the gate-negative pulse is relaxed by the holes, fewer hot holes are injected into the gate oxide film, and the TFT characteristics are less deteriorated.